TOSHIBA Field Effect Transistor Silicon P Channel Junction Type

2SJ74

Low Noise Audio Amplifier Applications

Unit: mm

- Recommended for first stages of EQ amplifiers and M.C. head amplifiers.
- High $|Y_{fs}|$: $|Y_{fs}| = 22 \text{ mS (typ.)}$ $(V_{DS} = -10 \text{ V}, V_{GS} = 0, I_{DSS} = -3 \text{ mA})$
- Low noise: $E_n = 0.95 \text{ nV/Hz}^{1/2} \text{ (typ.)}$

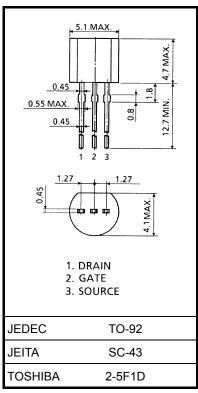
$$(V_{DS} = -10 \text{ V}, I_{D} = -1 \text{ mA}, f = 1 \text{ kHz})$$

- High input impedance: $I_{GSS} = 1.0 \text{ nA (max) (V}_{GS} = 25 \text{ V)}$
- Complimentary to 2SK170

Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Gate-drain voltage	V_{GDS}	25	V
Gate current	IG	-10	mA
Drain power dissipation	P _D	400	mW
Junction temperature	Tj	125	°C
Storage temperature range	T _{stg}	-55~125	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e.



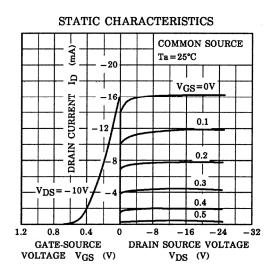
Weight: 0.21 g (typ.)

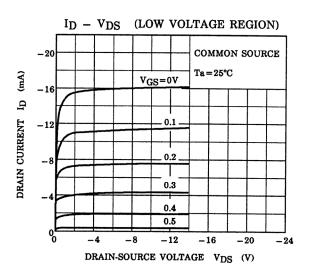
operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

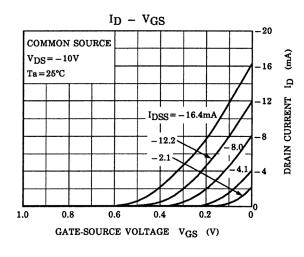
Electrical Characteristics (Ta = 25°C)

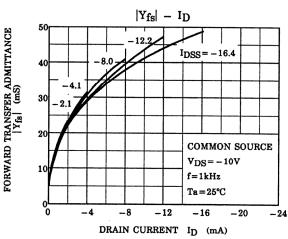
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate cut-off current	I _{GSS}	$V_{GS} = 25 \text{ V}, V_{DS} = 0$	_	_	1.0	nA
Gate-drain breakdown voltage	V _(BR) GDS	$V_{DS} = 0$, $I_G = 100 \mu A$	25			٧
Drain current	I _{DSS} (Note)	$V_{DS} = -10 \text{ V}, V_{GS} = 0$	-2.6		-20	mA
Gate-source cut-off voltage	V _{GS} (OFF)	$V_{DS} = -10 \text{ V}, I_D = -0.1 \mu\text{A}$	0.15	_	2.0	V
Forward transfer admittance	Y _{fs}	$V_{DS} = -10 \text{ V}, V_{GS} = 0, f = 1 \text{ kHz}$	8	22	_	mS
Input capacitance	C _{iss}	$V_{DS} = -10 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	_	105	_	pF
Reverse transfer capacitance	C _{rss}	$V_{DG} = -10 \text{ V}, I_D = 0, f = 1 \text{ MHz}$	_	32	_	pF
Noise figure –	NF (1)	$\begin{split} V_{DS} = -10 \text{ V}, \text{ I}_D = -1 \text{ mA}, \text{ R}_G = 1 \text{ k}\Omega, \\ f = 10 \text{ Hz} \end{split}$	_	1.0	10	- dB
	NG (2)	$V_{DS} = -10 \text{ V}, \text{ I}_{D} = -1 \text{ mA}, \text{ R}_{G} = 1 \text{ k}\Omega,$ f = 1 kHz	_	0.5	2	

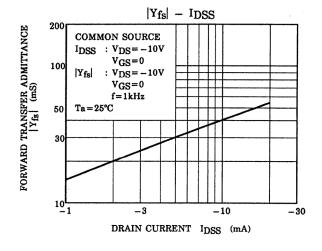
Note: I_{DSS} classification GR: -2.6~-6.5 mA, BL: -6.0~-12 mA, V: -10~-20 mA

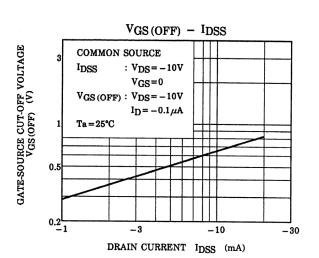


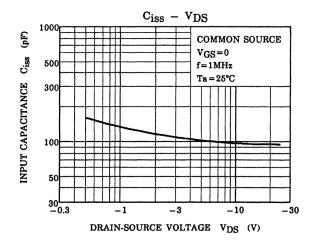


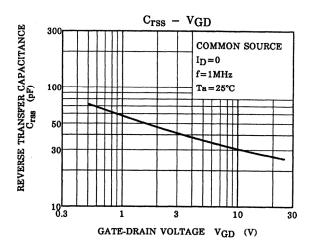


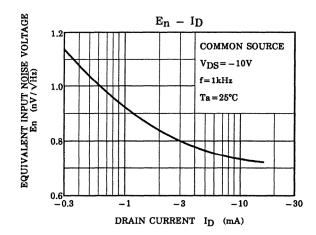


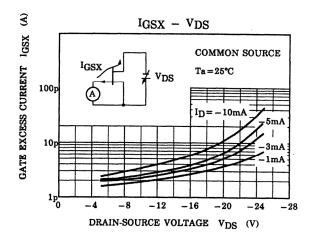


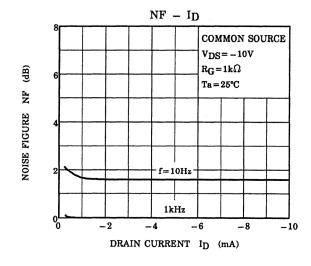


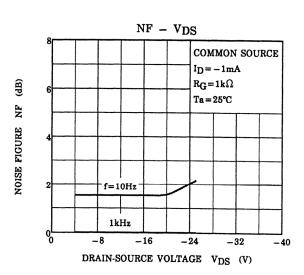


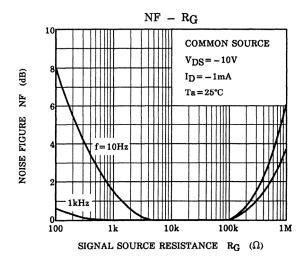


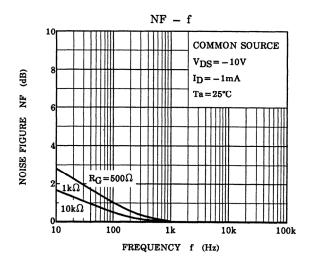












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20070701-EN GENERAL

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